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Static relay and communication device using static relay

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Fixed contacts (23A, 24A) are provided on the upper surface of a silicon substrate (21). Signal lines (23, 24) electrically continuous with the fixed contacts (23A, 24A) are provided so as to pass through a silicon substrate (21) from the reverse surface to the reverse surface thereof. Bumps (32, 33) electrically continuous with the signal lines (23, 24) are provided on the reverse surface of the silicon substrate (21). A fixed electrode (22) is provided on both sides of the fixed contacts (23A, 24A). Wiring conductors (30, 31) electrically continuous with the fixed electrode (22) are provided so as to pass through the silicon substrate (21) from the reverse surface to the reverse surface thereof. Bumps (34, 35) electrically continuous with the wiring conductors (30, 31) are provided on the reverse surface of the silicon substrate (21). Through holes (25, 27) of the silicon substrate (21) through which the signal lines (23, 24) are passed and through holes (28, 29) of the silicon substrate (21) through which the wiring conductors (30, 31) are passed are formed by etching the silicon substrate (21).

